# BLF8G24LS-100V; BLF8G24LS-100GV

**Power LDMOS transistor** 

**AMPLEON** 

Rev. 4 — 1 September 2015

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

100 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 2300 MHz to 2400 MHz.

Table 1. Typical performance

Typical RF performance at  $T_{case} = 25$  °C in a common source class-AB production test circuit.

Test signal	f	I <sub>Dq</sub>	V <sub>DS</sub>	P <sub>L(AV)</sub>	Gp	$\eta_D$	ACPR <sub>5M</sub>
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2300 to 2400	900	28	25	19	32	-29 <u>[1]</u>

<sup>[1]</sup> Test signal: 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF per carrier; 5 MHz carrier spacing.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth (90 MHz typical)
- Designed for broadband operation (2300 MHz to 2400 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

#### 1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF8G24LS-1	100V (SOT1244B)		
1	drain	4 1 5	4
2	gate	4 1 5	6,7→1 1 4,5
3	source [1]		2
4	decoupling lead	3	3
5	decoupling lead		aaa-003619
6	n.c.		
7	n.c.	6 2 7	
BLF8G24LS-1	100GV (SOT1244C)	•	
1	drain		,
2	gate	4 1 5	6.7→1 → 4,5
3	source [1]		6,7 - 4,5
4	decoupling lead		3
5	decoupling lead	6 2 7	aaa-003619
6	n.c.	3	
7	n.c.		

<sup>[1]</sup> Connected to flange.

## 3. Ordering information

Table 3. Ordering information

· · · · · · · · · · · · · · · · · · ·				
Type number	Packag	Package		
	Name	Description	Version	
BLF8G24LS-100V	-	earless flanged ceramic package; 6 leads	SOT1244B	
BLF8G24LS-100GV	-	earless flanged ceramic package; 6 leads	SOT1244C	

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-c)}}$	thermal resistance from junction to case	$T_{case} = 80  ^{\circ}C;  P_{L} = 48  W$	0.29	K/W

#### 6. Characteristics

#### Table 6. DC characteristics

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 153 mA	1.5	1.9	2.3	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 900 mA	1.6	2	2.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	4.2	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	29	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	420	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 153 mA	-	1.27	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5.35 \text{ A}$	-	0.1	-	Ω

#### Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on the CCDF;  $f_1$  = 2302.5 MHz;  $f_2$  = 2307.5 MHz;  $f_3$  = 2392.5 MHz;  $f_4$  = 2397.5 MHz; RF performance at RF performance at RF performance at RF production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L(AV)</sub> = 25 W	18	19	-	dB
$\eta_{D}$	drain efficiency	P <sub>L(AV)</sub> = 25 W	29	32	-	%
RLin	input return loss	P <sub>L(AV)</sub> = 25 W	-	-17	-7	dB
ACPR <sub>5M</sub>	adjacent channel power ratio (5 MHz)	P <sub>L(AV)</sub> = 25 W	-	-29	-25	dBc

#### 7. Test information

#### 7.1 Ruggedness in class-AB operation

The BLF8G24LS-100V and BLF8G24LS-100GV are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 28 V;  $I_{Dq}$  = 900 mA;  $P_{L}$  = 100 W; f = 2300 MHz.

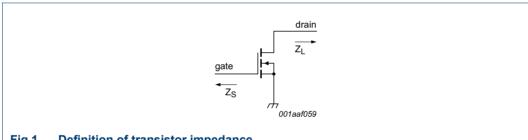
### 7.2 Impedance information

Table 8. **Typical impedance** 

Measured load-pull data;  $I_{Dq} = 900 \text{ mA}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]		
(MHz)	(Ω)	(Ω)		
BLF8G24LS-100V				
2300	1.52 – j4.32	1.96 – j2.21		
2400	2.54 – j5.05	1.83 – j2.03		
2500	4.83 – j5.28	1.76 – j2.23		
BLF8G24LS-100GV				
2300	1.60 – j5.88	1.96 – j4.12		
2400	2.53 – j6.66	1.81 – j4.12		
2500	4.53 – j7.28	1.74 – j4.33		

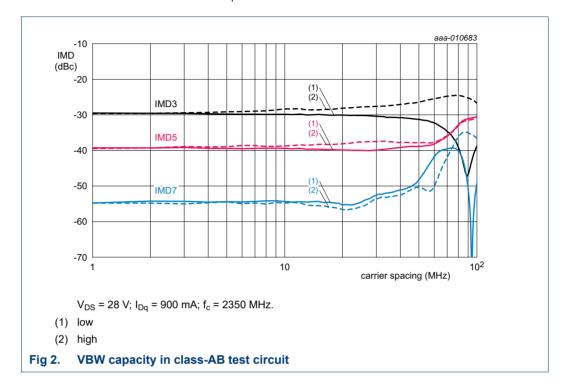
[1]  $Z_S$  and  $Z_L$  defined in Figure 1.



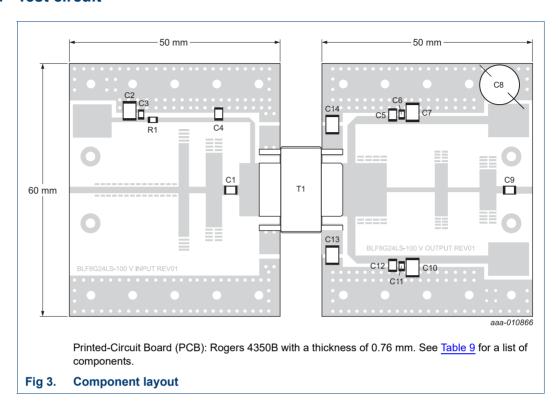
**Definition of transistor impedance** Fig 1.

#### 7.3 VBW in a class-AB operation

The BLF8G24LS-100V and BLF8G24LS-100GV show 90 MHz (typical) video bandwidth (IMD third-order intermodulation inflection point) in a class-AB test circuit in the 2.3 GHz to 2.4 GHz band at  $V_{DS}$  = 28 V and  $I_{Dq}$  = 0.9 A.



#### 7.4 Test circuit



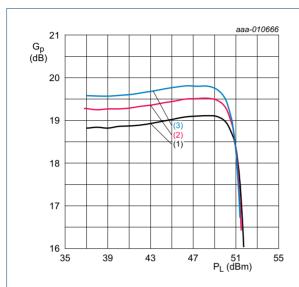
**Table 9. List of components** See Figure 3 for component layout.

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	1.0 pF [1]	ATC 800B
C2	multilayer ceramic chip capacitor	1 μF [2]	Murata
C3	multilayer ceramic chip capacitor	100 nF [2]	Murata
C4, C5, C9, C12	multilayer ceramic chip capacitor	24 pF [1]	ATC 800B
C6, C11	multilayer ceramic chip capacitor	220 nF [2]	Murata
C7, C10, C13, C14	multilayer ceramic chip capacitor	4.7 μF, 50 V	Murata
C8	electrolytic capacitor	> 470 μF, 63 V	
R1	chip resistor	4.7 Ω, 1 % tolerance	SMD 0805
T1	transistor	-	Ampleon BLF8G24LS-100V

- [1] American Technical Ceramics type 800B or capacitor of same quality.
- [2] Murata or capacitor of same quality.

#### 7.5 Graphical data

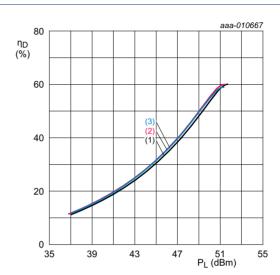
#### 7.5.1 Pulsed CW



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 900 mA;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 4. Power gain as a function of output power; typical values

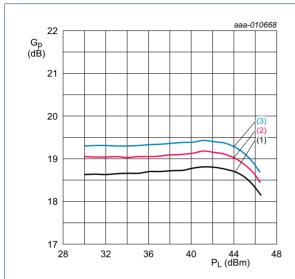


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 900 mA;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 5. Drain efficiency as a function of out power; typical values

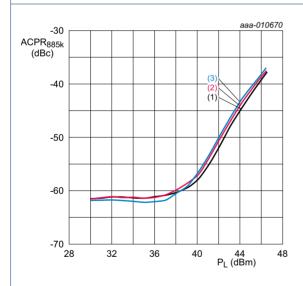
#### 7.5.2 IS-95



 $V_{DS} = 28 \text{ V}; I_{Dq} = 900 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

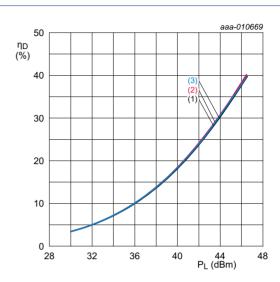
Fig 6. Power gain as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 900 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

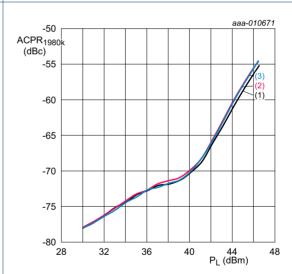
Fig 8. Adjacent channel power ratio (885 kHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 900 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 7. Drain efficiency as a function of output power; typical values

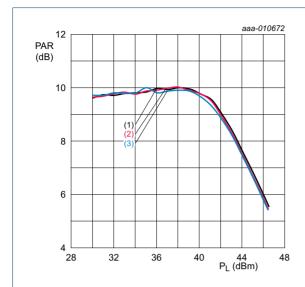


 $V_{DS} = 28 \text{ V}; I_{Dq} = 900 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 9. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values

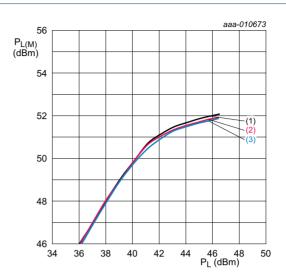
**Power LDMOS transistor** 



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 900 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 10. Peak-to-average ratio as a function of output power; typical values

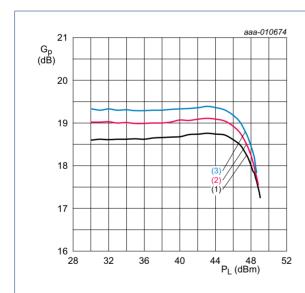


 $V_{DS} = 28 \text{ V}; I_{Dq} = 900 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 11. Peak output power as a function of output power; typical values

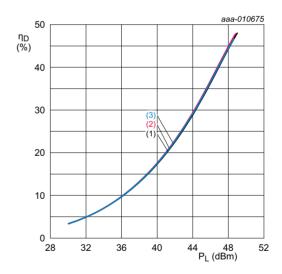
#### 7.5.3 1-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 900 \text{ mA}.$ 

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 12. Power gain as a function of output power; typical values

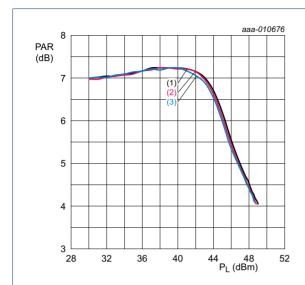


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 900 mA.

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 13. Drain efficiency as a function of output power; typical values

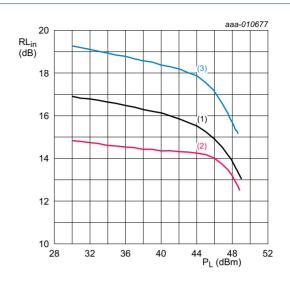
**Power LDMOS transistor** 



 $V_{DS} = 28 \text{ V}; I_{Dq} = 900 \text{ mA}.$ 

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 14. Peak-to-average ratio as a function of output power; typical values

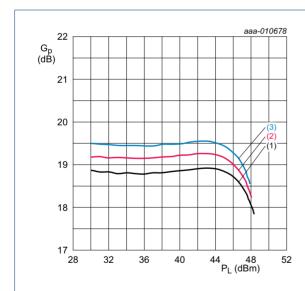


 $V_{DS} = 28 \text{ V}; I_{Dq} = 900 \text{ mA}.$ 

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 15. Input return loss as a function of output power; typical values

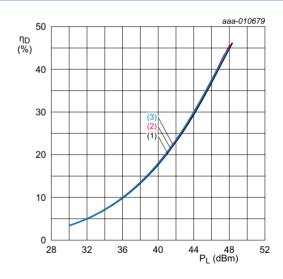
#### 7.5.4 2-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 900 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 16. Power gain as a function of output power; typical values

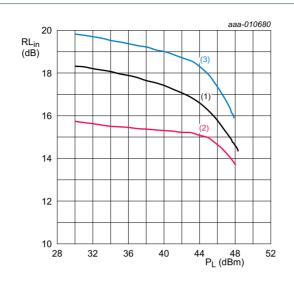


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 900 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 17. Drain efficiency as a function of output power; typical values

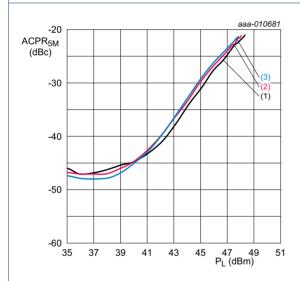
**Power LDMOS transistor** 



 $V_{DS} = 28 \text{ V}; I_{Dq} = 900 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

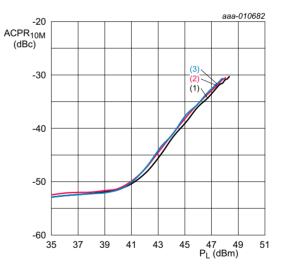
Fig 18. Input return loss as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 900 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 19. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 900 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 20. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

## 8. Package outline

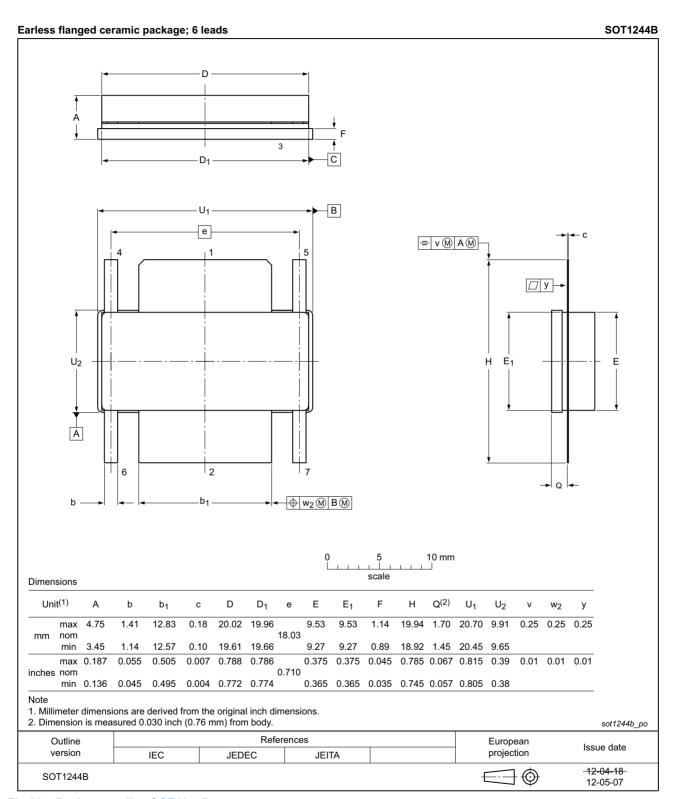


Fig 21. Package outline SOT1244B

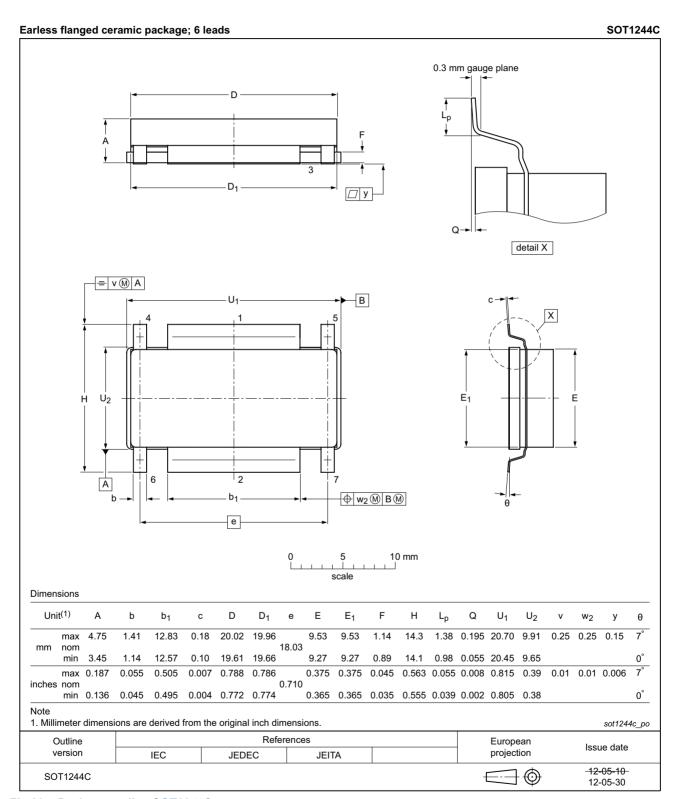


Fig 22. Package outline SOT1244C

## 9. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

#### 10. Abbreviations

Table 10. Abbreviations

Acronym	Description	
3GPP	3rd Generation Partnership Project	
CCDF	Complementary Cumulative Distribution Function	
CW	Continuous Wave	
DPCH	Dedicated Physical CHannel	
ESD	ElectroStatic Discharge	
IS-95	Interim Standard 95	
LDMOS	Laterally Diffused Metal Oxide Semiconductor	
MTF	Median Time to Failure	
PAR	Peak-to-Average Ratio	
SMD	Surface Mounted Device	
VBW	Video BandWidth	
VSWR	Voltage Standing Wave Ratio	
W-CDMA	Wideband Code Division Multiple Access	

## 11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF8G24LS-100V_24LS-100GV#4	20150901	Product data sheet		BLF8G24LS-100V_ 24LS-100GV v.3
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of Ampleon.</li> <li>Legal texts have been adapted to the new company name where appropriate</li> </ul>			
BLF8G24LS-100V_24LS-100GV v.3	20140627	Product data sheet	-	BLF8G24LS-100V_ 24LS-100GV v.2
BLF8G24LS-100V_24LS-100GV v.2	20140228	Objective data sheet	-	BLF8G24LS-100V_ 24LS-100GV v.1
BLF8G24LS-100V_24LS-100GV v.1	20131104	Objective data sheet	-	-

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition		
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.		
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.		
Product [short] data sheet	Production	This document contains the product specification.		

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

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BLF8G24LS-100V 24LS-100GV#4

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**Power LDMOS transistor** 

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#### 13. Contact information

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

## **AMPLEON**

## BLF8G24LS-100(G)V

**Power LDMOS transistor** 

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